EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	("NAND") and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:01
L3	2	(((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source adj slot) and (drain adj contact) and (source adj select adj (gate or electrode)) and (drain adj select adj (gate or electrode)) and ((single or one) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:04
L4	271	(((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single or one) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:05
L5	144	(((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:22
L6	144	(((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:06

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L7	0	(((((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) with ((single or one) adj mask$4)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:23
L8	0	(((((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) near ((single or one) adj mask$4)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:23
L9	2	(((((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) same ((single or one) adj mask$4)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:24
L10	144	(((((memory adj array) or (("NAND") adj flash adj memory)) or ((field adj effect adj transistor) or ("FET"))) and (source) and (drain) and (source adj (gate or electrode or contact)) and (drain adj (gate or electrode or contact))) and ((single or one) adj mask$4)) and ((single) adj mask$4) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 10:25
S1	1863	NAND with source with drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:24

EAST Search History

S2	1359	(NAND with source with drain) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:25
S3	31	(NAND with source with drain) and semiconductor and slot and contact and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/04 09:47
S5	4	(NAND with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:19
S6	159	((memory adj cell) with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:24
S7	4	(("20020149081") or ("6115287") or ("6411548") or ("5780338")).PN.	US-PGPUB; USPAT	OR	OFF	2005/03/24 14:00
S8	0	(((memory adj cell) with source with drain) with (single adj mask$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:24
S9	0	(NAND with source with drain with (single adj mask$6)) and semiconductor and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:25
S10	0	(NAND with source with drain with (single adj mask$6)) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:25

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S11	2226	(438/586).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/27 10:19
S12	0	438/586.ccls. and (NAND with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:37
S13	1	"438"/$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:20
S14	4	"257"/$.ccls. and (NAND with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:24
S15	0	("257"/$.ccls. with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:25
S16	0	("438"/$.ccls. with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:25
S17	0	(("438"/$.ccls.) with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:25
S18	0	(("257"/$.ccls.) with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26

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S19	0	(("257"/$.ccls.) with source with drain) and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/27 10:26
S20	0	(("438"/$.ccls.) with source with drain) and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:45
S21	0	(("438"/$.ccls.) with source with drain) and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:45
S22	6	((NAND) with source with drain) and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/19 06:55
S23	6	(("20020149081") or ("6115287") or ("6411548")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/19 06:55
S24	2218	("NAND") with source with drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:25
S25	40	("NAND") with source with drain with mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:28
S26	3	("NAND") with source with drain with (single adj mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:25

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S27	36	(("NAND") with source with drain with mask) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:28
S28	1	438/586.ccls. and (NAND with source with drain) and semiconductor and (single adj mask$6) and @ad<="20031023"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/27 12:38